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# Discrete POWER & Signal **Technologies**

# 2N5962







# **NPN General Purpose Amplifier**

This device is designed for use as low noise, high gain, general purpose amplifiers requiring collector currents to 50 mA. Sourced from Process 07. See 2N5088 for characteristics.

# **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	45	V
V <sub>CBO</sub>	Collector-Base Voltage	45	V
$V_{EBO}$	Emitter-Base Voltage	8.0	V
Ic	Collector Current - Continuous	100	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

# **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic Max		Units	
		2N5962	*MMBT5962	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

<sup>1)</sup> These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# NPN General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_C = 5.0 \text{ mA}, I_B = 0$	45		V
/ <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10  \mu A, I_E = 0$	45		V
/ <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10  \mu A, I_C = 0$	8.0		V
СВО	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		2.0	nA
	5 % 0 . # 0	$V_{CB} = 30 \text{ V}, I_{E} = 0, T_{A} = 65 ^{\circ}\text{C}$		50	nA
EBO	Emitter Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		1.0	nA
ON CHAF	RACTERISTICS*				
) <sub>FE</sub>	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A}$	450		
		$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$	500		
		$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$	550 600	1400	
/ <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	000	0.2	V
BE(on)	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	0.5	0.7	V
/ <sub>BE(on)</sub> SMALL S	-	-	0.5	4.0	V
SMALL S	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	0.5		
SMALL S	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}$ $V_{EB} = 0.5 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$	0.5	4.0	pF
SMALL S	Base-Emitter On Voltage  BIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}$ $V_{EB} = 0.5 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$	600	4.0	pF
SMALL S	Base-Emitter On Voltage  BIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}$ $V_{EB} = 0.5 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$		4.0	pF
SMALL S	Base-Emitter On Voltage  BIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}$ $V_{EB} = 0.5 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$	600	4.0	pF
SMALL S	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ \\ V_{CB} &= 5.0 \text{ V} \\ \\ V_{EB} &= 0.5 \text{ V} \\ \\ I_{C} &= 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ I_{C} &= 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 10 \text{ \muA}, \\ R_{S} &= 10 \text{ k}\Omega, \text{ f} = 1.0 \text{ kHz}, \end{split}$	600	4.0 6.0 200	pF pF
SMALL S	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ \\ V_{CB} &= 5.0 \text{ V} \\ \\ V_{EB} &= 0.5 \text{ V} \\ \\ I_{C} &= 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ I_{C} &= 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ R_{S} &= 10 k\Omega, f = 1.0 \text{ kHz}, \\ B_{W} &= 400 \text{ Hz} \end{split}$	600	4.0	pF
SMALL S	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \end{split}$	600	4.0 6.0 200	pF pF
SMALL S	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ \\ V_{CB} &= 5.0 \text{ V} \\ \\ V_{EB} &= 0.5 \text{ V} \\ \\ I_{C} &= 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ I_{C} &= 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ R_{S} &= 10 k\Omega, f = 1.0 \text{ kHz}, \\ B_{W} &= 400 \text{ Hz} \end{split}$	600	4.0 6.0 200	pF pF
SMALL S	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz}, \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz}, \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \end{split}$	600	4.0 6.0 200	pF pF
SMALL S	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \end{split}$	600	4.0 6.0 200 3.0 6.0	pF pF dB
SMALL S	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ \end{split}$	600	4.0 6.0 200	pF pF
SMALL S	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \end{split}$	600	4.0 6.0 200 3.0 6.0 4.0	pF pF dB dB
SMALL S	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 100 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ \end{split}$	600	4.0 6.0 200 3.0 6.0	pF pF dB
J <sub>BE(on)</sub>	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ \end{split}$	600	4.0 6.0 200 3.0 6.0 4.0	pF pF dB dB

<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

#### **TO-92 Tape and Reel Data** FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: Label 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

# TO-92 Tape and Reel Data, continued

## **TO-92 Reeling Style** Configuration: Figure 2.0

#### Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

# Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

## **TO-92 Radial Ammo Packaging** Configuration: Figure 3.0



FIRST WIRE OFF IS EMITTER (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON BOTTOM



FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP



# **TO-92 Package Dimensions**



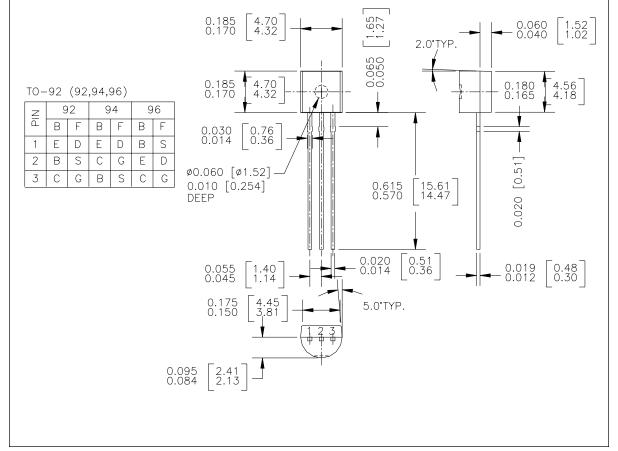
# TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977

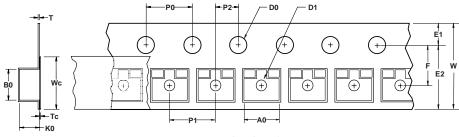




# SOT-23 Tape and Reel Data, continued

# **SOT-23 Embossed Carrier Tape**

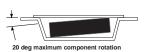
Configuration: Figure 3.0



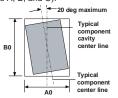
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

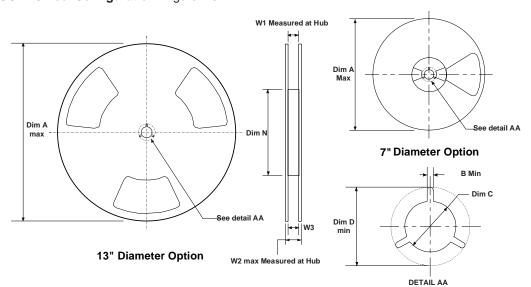


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

# SOT-23 Reel Configuration: Figure 4.0



	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9



# SOT-23 (FS PKG Code 49)

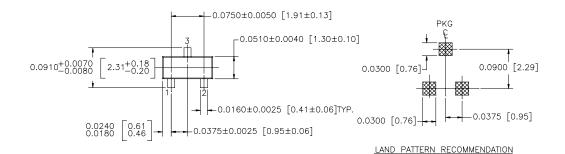


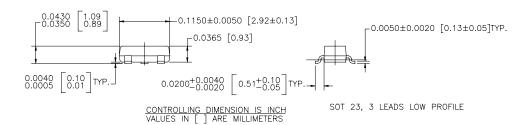


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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